

Amendments to the Claims:

The following listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A transistor comprising:

a ferromagnetic source that is formed with a ferromagnetic body from which spin-polarized conduction carriers are injected;

a ferromagnetic drain that is formed with a ferromagnetic body that receives the spin-polarized conduction carriers injected from the ferromagnetic source;

a semiconductor layer that is provided between the ferromagnetic source and the ferromagnetic drain, and forms a Schottky junction having a Schottky barrier at each junction interface with the ferromagnetic source and the ferromagnetic drain; and

a gate electrode that is formed associated with the semiconductor layer.

wherein the Schottky barrier appears on the conduction band side when the spin-polarized conduction carriers are electrons, and the Schottky barrier appears on the valence band side when the spin-polarized conduction carriers are holes, with the spin-polarized conduction carriers being of the same conduction type as that of the semiconductor layer (an accumulation channel type).

2. (Original) The transistor as claimed in claim 1, wherein the magnetization direction of the ferromagnetic source or the ferromagnetic drain is inverted, so that the relative magnetization direction of the ferromagnetic drain is made equal (“parallel magnetization”) to or opposite (“antiparallel magnetization”) to the magnetization direction of the ferromagnetic source.

3. (Original) The transistor as claimed in claim 1, wherein the ferromagnetic source and the ferromagnetic drain are made of a ferromagnetic metal.

4. (Canceled).

5. (Currently Amended) A transistor comprising:

a ferromagnetic source that is formed with a ferromagnetic body from which spin-polarized conduction carriers are injected;

a ferromagnetic drain that is formed with a ferromagnetic body that receives the spin-polarized conduction carriers injected from the ferromagnetic source;

a semiconductor layer that is provided between the ferromagnetic source and the ferromagnetic drain, and forms a Schottky junction having a Schottky barrier at each junction interface with the ferromagnetic source and the ferromagnetic drain; and

a gate electrode that is formed associated with the semiconductor layer, The transistor as claimed in claim 1,

wherein the Schottky barrier appears on the valence band side when the spin-polarized conduction carriers are electrons, and the Schottky barrier appears on the conduction band side when the spin-polarized conduction carriers are holes, with the spin-polarized conduction carriers being of a different conduction type from that of the semiconductor layer (an inversion channel type), the semiconductor layer not having an inversion layer formed therein.

6. (Currently Amended) The transistor as claimed in claim 4, claim 1, wherein, with a voltage not being applied between the gate electrode and the ferromagnetic source, the Schottky barrier restrains the spin-polarized conduction carriers from being injected to the semiconductor layer due to tunneling and heat radiation, the transistor being of the accumulation channel type.

7. (Currently Amended) The transistor as claimed in claim 4, claim 1, wherein a voltage is applied to the gate electrode, so that the spin-polarized conduction carriers of the ferromagnetic source are injected to the semiconductor layer by tunneling the Schottky barrier

at the interface between the ferromagnetic source and the semiconductor layer, the transistor being of the accumulation channel type.

8. (Currently Amended) The transistor as claimed in claim 4, claim 1, wherein, with a voltage not being applied to the gate electrode, the Schottky barrier restrains the spin-polarized conduction carriers from being injected to the semiconductor layer due to heat radiation, while the spin-polarized conduction carriers of the ferromagnetic source are injected to the semiconductor layer by tunneling the Schottky barrier, the transistor being of the accumulation channel type.

9. (Currently Amended) The transistor as claimed in claim 4, claim 1, wherein, with a voltage being applied to the gate electrode, the spin-polarized conduction carriers of the ferromagnetic source tunnels the Schottky barrier at the interface between the ferromagnetic source and the semiconductor layer, so as to control a current that is generated between the ferromagnetic source and the ferromagnetic drain, the transistor being of the accumulation channel type.

10. (Original) The transistor as claimed in claim 5, wherein, with a voltage not being applied between the gate electrode and the ferromagnetic source, the Schottky barrier restrains the spin-polarized conduction carriers from being injected to the semiconductor layer due to tunneling and heat radiation, the transistor being of the inversion channel type.

11. (Original) The transistor as claimed in claim 5, wherein a voltage is applied to the gate electrode to form an inversion layer in the semiconductor layer, so that the spin-polarized conduction carriers of the ferromagnetic source are injected to the semiconductor layer due to at least one of heat radiation and tunneling, the transistor being of the inversion channel type.

12. (Original) The transistor as claimed in claim 5, wherein, even with a voltage not being applied to the gate electrode, an inversion layer is formed in the semiconductor

layer, and the spin-polarized conduction carriers of the ferromagnetic source are injected to the semiconductor layer due to at least one of heat radiation and tunneling, the transistor being of the inversion channel type.

13. (Original) The transistor as claimed in claim 5, wherein, with a voltage being applied to the gate electrode, the spin-polarized conduction carriers of the ferromagnetic source are injected from the ferromagnetic source to the semiconductor layer due to at least one of heat radiation and tunneling, so as to control a current generated between the ferromagnetic source and the ferromagnetic drain, the transistor being of the inversion channel type.

14. (Currently Amended) The transistor as claimed in ~~claim 4, claim 1~~, wherein the spin-polarized conduction carriers injected to the semiconductor layer are spin-polarized in accordance with the spin polarization rate at the Fermi energy of the ferromagnetic source, the transistor being of the accumulation channel type or the inversion channel type.

15. (Currently Amended) The transistor as claimed in ~~claim 4, claim 1~~, wherein:

when the relative magnetization state between the ferromagnetic source and the ferromagnetic drain is parallel magnetization, an electric resistance due to spin-dependent scattering of the spin-polarized conduction carriers injected from the ferromagnetic source is low in the ferromagnetic drain;

when the relative magnetization state between the ferromagnetic source and the ferromagnetic drain is antiparallel magnetization, the electric resistance due to spin-dependent scattering of the spin-polarized conduction carriers injected from the ferromagnetic source is high in the ferromagnetic drain,

the transistor being of the accumulation channel type or the inversion channel type.

16. (Original) The transistor as claimed in claim 1, wherein turns-conductance can be controlled in accordance with the relative magnetization direction of the ferromagnetic drain with respect to the ferromagnetic source, with the same bias being applied.

17. (Currently Amended) The transistor as claimed in ~~claim 4, claim 1~~, wherein, when the ferromagnetic source and the ferromagnetic drain exhibit parallel magnetization, the transistor has a threshold voltage that is defined as a gate voltage for generating a predetermined current between the ferromagnetic source and the ferromagnetic drain, with a voltage being applied to the gate electrode,

the transistor being of the accumulation channel ~~type or the inversion channel~~ type.

18. (Withdrawn) A transistor comprising:

a ferromagnetic source that is made of a half metal exhibiting a metallic band structure for one of the spins (“metallic spin band”) while exhibiting a semiconductor-like or insulator-like band structure for the other spin (“semiconductor spin band”), the half metal being a ferromagnetic body, spin-polarized conduction carriers being injected from the ferromagnetic source;

a ferromagnetic drain that is made of a half metal and receives the spin-polarized conduction carriers injected from the ferromagnetic source;

a semiconductor layer that is provided between the ferromagnetic source and the ferromagnetic drain, and is joined to the ferromagnetic source and the ferromagnetic drain; and

a gate electrode that is formed associated with the semiconductor layer.

19. (Withdrawn) The transistor as claimed in claim 18, wherein the ferromagnetic source and the ferromagnetic drain form a Schottky junction having a Schottky barrier at the interface between the semiconductor layer and the metallic spin band in the half metal.

20. (Withdrawn) The transistor as claimed in claim 18, wherein:

with the conduction carriers having the same conduction type as the conduction type of the semiconductor layer (“accumulation channel type”),

when the conduction carriers are electrons, the Schottky barrier formed by the metallic spin band appears on the conduction band side; and

when the conduction carriers are holes, the Schottky barrier formed by the metallic spin band appears on the valence band side.

21. (Withdrawn) The transistor as claimed in claim 18, wherein:

with the conductive carriers having a different conduction type from the conduction type of the semiconductor layer (“inversion channel type”), the semiconductor layer not having an inversion layer formed therein,

when the conduction carriers are electrons, the Schottky barrier appears on the valence band side; and

when the conduction carriers are holes, the Schottky barrier appears on the conduction band side.

22. (Withdrawn) The transistor as claimed in claim 18, wherein, at the junction between the semiconductor layer and the ferromagnetic source and drain, the semiconductor spin band of the half metal has a wider band gap than the band gap of the semiconductor layer.

23. (Withdrawn) The transistor as claimed in claim 18, wherein:

at the junction between the semiconductor layer and the ferromagnetic source and drain,

the semiconductor spin band of the half metal forms an energy barrier against the semiconductor layer;

when the conduction carriers are electrons, the energy barrier appears at least on the conduction side; and

when the conduction carriers are holes, the energy barrier appears at least on the valence band side.

24. (Withdrawn) The transistor as claimed in claim 18, further comprising a contact (a "non-magnetic contact") that is made of a non-magnetic metal or a non-magnetic conductor formed associated with the ferromagnetic source and the ferromagnetic drain.

25. (Withdrawn) The transistor as claimed in claim 24, wherein:

the non-magnetic contact forms a junction between metals or an ohmic junction associated with the metallic spin band; and

the non-magnetic contact forms a junction structure between a semiconductor and a metal serving as an energy barrier, or between a metal and an insulator, associated with the semiconductor spin band.

26. (Withdrawn) The transistor as claimed in claim 20, wherein, with a voltage not being applied between the gate electrode and the ferromagnetic source, the Schottky barrier formed by the metallic spin band restrains the conduction carriers in the metallic spin band from being injected to the semiconductor layer due to tunneling and heat radiation,

the transistor being of the accumulation channel type.

27. (Withdrawn) The transistor as claimed in claim 20, wherein, with a voltage being applied to the gate electrode, the conduction carriers in the metallic spin band of the ferromagnetic source tunnel the Schottky barrier formed at the interface between the ferromagnetic source and the semiconductor layer, and are injected to the semiconductor layer,

the transistor being of the accumulation channel type.

28. (Withdrawn) The transistor as claimed in claim 20, wherein:

with a voltage not being applied to the gate electrode,
the Schottky barrier restrains the conduction carriers in the metallic spin band
from being injected to the semiconductor layer due to heat radiation; and
the conduction carriers in the metallic spin band of the ferromagnetic source
tunnel the Schottky barrier and are then injected to the semiconductor layer,
the transistor being of the accumulation channel type.

29. (Withdrawn) The transistor as claimed in claim 20, wherein

with a voltage being applied to the gate electrode,
the conduction carriers in the metallic spin band of the ferromagnetic source
tunnel the Schottky barrier formed at the interface between the ferromagnetic source and the
semiconductor layer, so as to control a current that is generated between the ferromagnetic
source and the ferromagnetic drain,
the transistor being of the accumulation channel type.

30. (Withdrawn) The transistor as claimed in claim 20, wherein the energy barrier
formed by the semiconductor spin band due to the non-magnetic contact restrains conduction
carriers that have spins parallel to the semiconductor spin band of the ferromagnetic source
from being injected to the semiconductor layer due to tunneling and heat radiation, the
conduction carriers being injected from the non-magnetic contact formed along the
ferromagnetic source,
the transistor being of the accumulation channel type.

31. (Withdrawn) The transistor as claimed in claim 21, wherein, with a voltage not
being applied between the gate electrode and the ferromagnetic source, the Schottky barrier
restrains the conduction carriers in the metallic spin band from being injected to the
semiconductor layer due to tunneling and heat radiation,

the transistor being of the inversion channel type.

32. (Withdrawn) The transistor as claimed in claim 21, wherein, with a voltage being applied to the gate voltage so as to form an inversion layer in the semiconductor layer, the conduction carriers in the metallic spin band of the ferromagnetic source are injected from the ferromagnetic source to the semiconductor layer due to at least one of heat radiation and tunneling,

the transistor being of the inversion channel type.

33. (Withdrawn) The transistor as claimed in claim 21, wherein:

with a voltage not being applied to the gate electrode,

the semiconductor layer has an inversion layer formed therein; and

the conduction carriers in the metallic spin band of the ferromagnetic source are injected to the semiconductor layer due to at least one of heat radiation and tunneling,

the transistor being of the inversion channel type.

34. (Withdrawn) The transistor as claimed in claim 21, wherein, with a voltage being applied to the gate electrode, the conduction carriers in the metallic spin band of the ferromagnetic source are injected from the ferromagnetic source to the semiconductor layer due to at least one of heat radiation and tunneling,

the transistor being of the inversion channel type.

35. (Withdrawn) The transistor as claimed in claim 21, wherein the energy barrier formed by the semiconductor spin band due to the non-magnetic contact restrains conduction carriers that have spins parallel to the semiconductor spin band of the ferromagnetic source from being injected to the semiconductor layer due to tunneling and heat radiation, the conduction carriers being injected from the non-magnetic contact formed along the ferromagnetic source,

the transistor being of the inversion channel type.

36. (Withdrawn) The transistor as claimed in claim 20, wherein the spin polarization rate of conduction carriers that is determined by the ratio of the number of conduction carriers having one of the spins injected from the metallic spin band of the ferromagnetic source to the semiconductor layer to the number of conduction carriers having the other one of the spins injected from the non-magnetic contact, formed as opposed to the ferromagnetic source, to the semiconductor layer via the semiconductor spin band of the ferromagnetic source, can be controlled by adjusting the energy gap of the semiconductor spin band of the ferromagnetic source or the height of a barrier formed with the semiconductor spin band of the ferromagnetic source or the film thickness of the ferromagnetic source, the barrier height being seen from the non-magnetic contact,
the transistor being of the accumulation channel type or the inversion channel type.

37. (Withdrawn) The transistor as claimed in claim 20, wherein:
when the relative magnetization state between the ferromagnetic source and the ferromagnetic drain is parallel magnetization, the metallic spin band of the ferromagnetic drain can conduct the conduction carriers injected from the metallic spin band of the ferromagnetic source to the semiconductor layer; and
when the relative magnetization state between the ferromagnetic source and the ferromagnetic drain is antiparallel magnetization, the energy barrier formed by the semiconductor spin band of the ferromagnetic drain restrains the conduction carriers, injected from the metallic spin band of the ferromagnetic source to the semiconductor layer, from conduction,
the transistor being of the accumulation channel type or the inversion channel type.

38. (Withdrawn) The transistor as claimed in claim 20, wherein, when the ferromagnetic source and the ferromagnetic drain exhibit parallel magnetization, the transistor has a threshold voltage that is defined as a gate voltage for generating a predetermined current between the ferromagnetic source and the ferromagnetic drain, with a voltage being applied to the gate electrode,

the transistor being of the accumulation channel type or the inversion channel type.

39. (Withdrawn) The transistor as claimed in claim 18, wherein turns-conductance can be controlled in accordance with the relative magnetization direction of the ferromagnetic drain with respect to the ferromagnetic source, with the same bias being applied.

40. (Original) The transistor as claimed in claim 1, wherein the ferromagnetic source and the ferromagnetic drain are formed through growth or deposition on the semiconductor layer.

41. (Original) The transistor as claimed in claim 1, wherein the ferromagnetic source and the ferromagnetic drain are by introducing magnetic elements into the semiconductor layer.

42. (Withdrawn) A memory device comprising
the transistor as claimed in claim 1,
using the transistor, information being stored in accordance with the relative magnetization direction of the ferromagnetic drain with respect to the ferromagnetic source,
the information stored in the transistor being detected based on the turns-conductance of the transistor depending on the relative magnetization direction of the ferromagnetic drain with respect to the ferromagnetic source.

43. (Withdrawn) A memory device comprising:
the transistor as claimed in claim 1;

a first line that is connected to the gate electrode;
a second line that is connected to the ferromagnetic drain; and
a third line that grounds the ferromagnetic source.

44. (Withdrawn) A memory device comprising:

the transistor as claimed in claim 1;
a first line that is connected to the gate electrode;
a second line that is connected to the ferromagnetic drain;
a third line that grounds the ferromagnetic source;
an output terminal that is formed at one end of the second line; and
a fourth line that branches from the second line and is connected to a power source via a load.

45. (Withdrawn) The memory device as claimed in claim 43, further comprising a first extra line and a second extra line that cross each other on the transistor or in the vicinity of the transistor, being electrically insulated.

46. (Withdrawn) The memory device as claimed in claim 43, wherein the first extra line and the second extra line, or one of the first extra line and the second extra line is replaced with the first line and the second line, or one of the first line and the second line.

47. (Withdrawn) The memory device as claimed in claim 45, wherein the magnetization of the ferromagnetic source or the ferromagnetic drain is inverted by a magnetic field that is induced by applying a current to the first extra line and the second extra line, or the first line and the second line that replace the first extra line and the second extra line, or one of the first line and the second line that replaces one of the first extra line and the second extra line and the other one of the first extra line and the second extra line that is not replaced, so that the relative magnetization state between the ferromagnetic source and the ferromagnetic drain is changed to rewrite information.

48. (Withdrawn) The memory device as claimed in claim 43, wherein:

when the ferromagnetic source and the ferromagnetic drain exhibit parallel magnetization, a voltage that is higher than the threshold voltage is applied to the first line; and

information is read out, based on the size of a drain current at the transistor when a predetermined bias is applied between the ferromagnetic source and the ferromagnetic drain.

49. (Withdrawn) The memory device as claimed in claim 44, wherein information is read out with an output voltage that is obtained based on a voltage drop due to the load caused by a drain current generated at the transistor when a voltage higher than the threshold voltage is applied to the gate electrode via the first line, the ferromagnetic source and the ferromagnetic drain exhibiting parallel magnetization.

50. (Withdrawn) A memory circuit comprising:

the transistors as claimed in claim 1, the transistors being arranged in a matrix fashion;

first lines that ground the respective ferromagnetic sources;

a plurality of word lines that connect the respective gate electrodes of the transistors that are arranged in the column direction; and

a plurality of bit lines that connect the respective ferromagnetic drains of the transistors that are arranged in the row direction.

51. (Withdrawn) A memory circuit comprising:

the transistors as claimed in claim 1, the transistors being arranged in a matrix fashion;

first lines that ground the respective ferromagnetic sources;

a plurality of word lines that connect the respective gate electrodes of the transistors that are arranged in the column direction;

a plurality of bit lines that connect the respective ferromagnetic drains of the transistors that are arranged in the row direction;

output terminals each formed at one end of each of the bit lines; and

second lines that branch from the respective bit lines and are connected to a power source via a load.

52. (Withdrawn) The memory circuit as claimed in claim 50, further comprising a first extra line and a second extra line that crosses each other on each of the transistors or in the vicinity of each of the transistors, the first extra line and the second extra line being electrically insulated.

53. (Withdrawn) The memory circuit as claimed in claim 52, wherein the first extra line and the second extra line, or one of the first extra line and the second extra line is replaced with the corresponding word line and the corresponding bit line, or one of the corresponding word line and the corresponding bit line.

54. (Withdrawn) The memory circuit as claimed in claim 50, wherein the magnetization of the ferromagnetic source or the ferromagnetic drain is inverted by a magnetic field that is induced by applying a current to the first extra line and the second extra line, or the word line and the bit line that replace the first extra line and the second extra line, or one of the word line and the bit line that replaces one of the first extra line and the second extra line and the other one of the first extra line and the second extra line that is not replaced, so that the relative magnetization state between the ferromagnetic source and the ferromagnetic drain is changed to rewrite information.

55. (Withdrawn) The memory circuit as claimed in claim 50, wherein:

when the ferromagnetic source and the ferromagnetic drain exhibit parallel magnetization, a voltage that is higher than the threshold voltage is applied to the word line; and

information is read out, based on the size of a drain current at the transistor when a predetermined bias is applied between the ferromagnetic source and the ferromagnetic drain.

56. (Withdrawn) The memory circuit as claimed in claim 51, wherein information is read out with an output voltage that is obtained based on a voltage drop due to the load caused by a drain current generated at the transistor when a voltage higher than the threshold voltage is applied to the gate electrode via the word line, the ferromagnetic source and the ferromagnetic drain exhibiting parallel magnetization.

57. (Withdrawn) The memory device or the memory circuit as claimed in claim 43, wherein information is rewritten by inverting the magnetization of the ferromagnetic source or the ferromagnetic drain.

58. (Withdrawn) A memory device comprising:

first and second transistors that are as claimed in claim 1;

a first line that collectively connects the gate electrode of the first transistor and the gate electrode of the second transistor;

a second line that is connected to a first ferromagnetic drain of the first transistor;

a third line that is connected to a second ferromagnetic drain of the second transistor; and

a fourth line that grounds the ferromagnetic source that is shared between the first and second transistors.

59. (Withdrawn) A memory circuit comprising

memory cells that are formed with the memory devices as claimed in claim 58, the memory cells being arranged in a matrix fashion.

60. (Original) The transistor as claimed in claim 1, wherein the semiconductor layer is an undoped semiconductor or an intrinsic semiconductor.

61. (Withdrawn) The transistor as claimed in claim 18, wherein the semiconductor layer is an undoped semiconductor or an intrinsic semiconductor.

62. (Currently Amended) The transistor as claimed in ~~claim 4, claim 1~~, wherein the semiconductor layer is an undoped semiconductor or an intrinsic semiconductor, the transistor being of the accumulation channel type.

63. (Original) The transistor as claimed in claim 5, wherein the semiconductor layer is an undoped semiconductor or an intrinsic semiconductor, the transistor being of the inversion channel type.

64. (Original) The transistor as claimed in claim 1, wherein a channel length that is defined as the length in the carrier conducting direction in the semiconductor layer or the distance between the ferromagnetic source and the ferromagnetic drain is so short that the semiconductor layer can conduct carriers in a ballistic manner, or the channel length is equal to or shorter than the mean free path associated with carrier energy relaxation.

65. (Original) The transistor as claimed in claim 1, further comprising a metal layer that forms a Schottky junction between the semiconductor layer and the metal layer, or a semiconductor layer that forms a Schottky junction between the ferromagnetic metal and the semiconductor layer, or a metal/semiconductor Schottky junction layer,

the metal layer, the semiconductor layer, or the metal/semiconductor Schottky layer being formed at the interface between the ferromagnetic metal and the semiconductor layer.

66. (Withdrawn) The transistor as claimed in claim 18, further comprising
a metal layer that forms a Schottky junction between the semiconductor layer
and the metal layer, or a semiconductor layer that forms a Schottky junction between the half
metal and the semiconductor layer, or a metal/semiconductor Schottky junction layer,
the metal layer, the semiconductor layer, or the metal/semiconductor Schottky
layer being formed at the interface between the half metal and the semiconductor layer.

67. (Original) The transistor as claimed in claim 60, wherein, when the relative
magnetization of the ferromagnetic drain with respect to the ferromagnetic source is
antiparallel magnetization, the drain current is lower than the drain current in a case of
parallel magnetization.

68. (Original) The transistor as claimed in claim 60, wherein turns-conductance
can be controlled in accordance with the relative magnetization direction of the ferromagnetic
drain with respect to the ferromagnetic source.

69. (Withdrawn) A memory device comprising
the transistor as claimed in claim 60,
using the transistor, information being stored in accordance with the relative
magnetization direction of the ferromagnetic drain with respect to the ferromagnetic source,
the information stored in the transistor being detected based on the turns-
conductance of the transistor depending on the relative magnetization direction of the
ferromagnetic drain with respect to the ferromagnetic source.

70. (Withdrawn) The memory device as claimed in claim 42, wherein the
semiconductor layer is an undoped semiconductor or an intrinsic semiconductor.

71. (Withdrawn) The memory circuit as claimed in claim 50, wherein the
semiconductor layer is an undoped semiconductor or an intrinsic semiconductor.

72. (Currently Amended) A transistor comprising:

a source and a drain that are of a first conduction type, and are formed with ferromagnetic semiconductors;

a semiconductor layer that is provided associated with the source and the drain, and has a channel of the first conduction type formed therein; and

a gate electrode that is formed as opposed to the semiconductor layer.
wherein the source and the drain are contacted with the semiconductor layer.

73. (Original) The transistor as claimed in claim 72, wherein the semiconductor layer is formed with an undoped semiconductor or an intrinsic semiconductor.

74. (Original) The transistor as claimed in claim 72, wherein a channel length that is defined as the length in the carrier conducting direction in the semiconductor layer or the distance between the ferromagnetic source and the ferromagnetic drain is so short that the semiconductor layer can conduct carriers in a ballistic manner, or the channel length is equal to or shorter than the mean free path associated with carrier energy relaxation.

75. (Currently Amended) A transistor comprising:

a source that is formed with a first pn junction between a first ferromagnetic semiconductor and a semiconductor layer that are of different conductive types from each other;

a drain that is formed with a second pn junction between a second ferromagnetic semiconductor and the semiconductor layer that are of different conductive types from each other; and

a gate electrode that is formed associated with the semiconductor layer.
wherein the semiconductor layer has a channel region.

76. (Original) The transistor as claimed in claim 75, wherein a channel length that is defined as the length in the carrier conducting direction in the semiconductor layer or the distance between the ferromagnetic source and the ferromagnetic drain is of such length that

the semiconductor layer can conduct carriers in a ballistic manner, or the channel length is equal to or shorter than the mean free path for carrier energy relaxation.

77. (Original) The transistor as claimed in claim 72, wherein, when the relative magnetization of the ferromagnetic drain with respect to the ferromagnetic source is antiparallel magnetization, the drain current is lower than the drain current in a case of parallel magnetization.

78. (Original) The transistor as claimed in claim 72, wherein turns-conductance can be controlled in accordance with the relative magnetization direction of the ferromagnetic drain with respect to the ferromagnetic source.

79. (Withdrawn) A memory device comprising
the transistor as claimed in claim 72,
using the transistor, information being stored in accordance with the relative magnetization direction of the ferromagnetic drain with respect to the ferromagnetic source,
the information stored in the transistor being detected based on the turns-conductance of the transistor depending on the relative magnetization direction of the ferromagnetic drain with respect to the ferromagnetic source.

80. (Withdrawn) The memory device as claimed in claim 42, wherein the a source and a drain that are of a first conduction type, and are formed with ferromagnetic semiconductors;

a semiconductor layer that is provided associated with the source and the drain, and has a channel of the first conduction type formed therein; and
a gate electrode that is formed as opposed to the semiconductor layer.

81. (Withdrawn) The memory circuit as claimed in claim 50, wherein the a source and a drain that are of a first conduction type, and are formed with ferromagnetic semiconductors;

a semiconductor layer that is provided associated with the source and the drain, and has a channel of the first conduction type formed therein; and
a gate electrode that is formed as opposed to the semiconductor layer.

82. (Currently Amended) A transistor comprising:

a ferromagnetic source that is formed with a ferromagnetic body from which spin-polarized conduction carriers;

a ferromagnetic drain that is formed with a ferromagnetic body and receives the spin-polarized conduction carriers injected from the ferromagnetic source;

a semiconductor layer that is provided between the ferromagnetic source and the ferromagnetic drain, and form junctions with the ferromagnetic source and the ferromagnetic drain; and

a gate electrode that is formed associated with the semiconductor layer,
wherein one of the ferromagnetic source and the ferromagnetic drain is formed of a ferromagnetic metal, and the other thereof is formed of a half metal.

83. (Original) The transistor as claimed in claim 1, wherein a gate insulating film formed between the gate electrode and the semiconductor layer is an insulator that is formed through oxidization or deposition.

84. (Original) The transistor as claimed in claim 83, wherein the gate insulating film contains a high dielectric constant material.

85. (Original) The transistor as claimed in claim 1, wherein the transistor is a MISFET.

86. (Original) The transistor as claimed in claim 1, wherein an impurity is added to the semiconductor layer, so that the transistor functions as a depletion-mode transistor.